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### Understanding [Embedded - FPGAs \(Field Programmable Gate Array\)](#)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

### Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

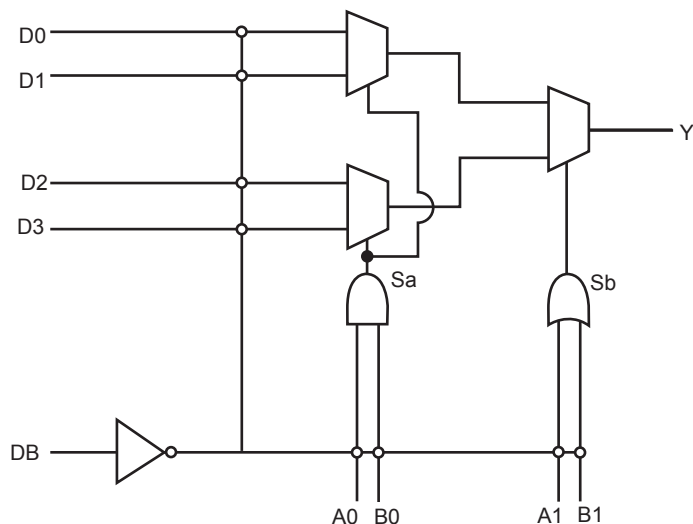
#### Details

Product Status	Active
Number of LABs/CLBs	-
Number of Logic Elements/Cells	256
Total RAM Bits	-
Number of I/O	70
Number of Gates	6000
Voltage - Supply	2.3V ~ 2.7V
Mounting Type	Surface Mount
Operating Temperature	-40°C ~ 125°C (TA)
Package / Case	100-LQFP
Supplier Device Package	100-TQFP (14x14)
Purchase URL	<a href="https://www.e-xfl.com/product-detail/microchip-technology/ex128-tqg100a">https://www.e-xfl.com/product-detail/microchip-technology/ex128-tqg100a</a>

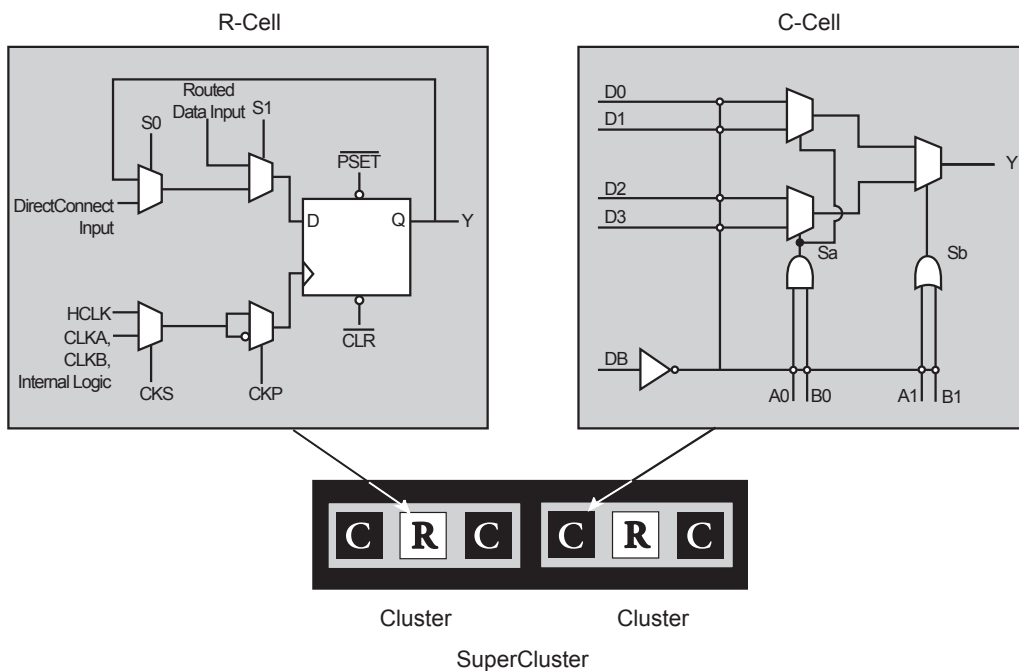
## Module Organization

C-cell and R-cell logic modules are arranged into horizontal banks called Clusters, each of which contains two C-cells and one R-cell in a C-R-C configuration.

Clusters are further organized into modules called SuperClusters for improved design efficiency and device performance, as shown in Figure 1-3. Each SuperCluster is a two-wide grouping of Clusters.



**Figure 1-2 • C-Cell**



**Figure 1-3 • Cluster Organization**

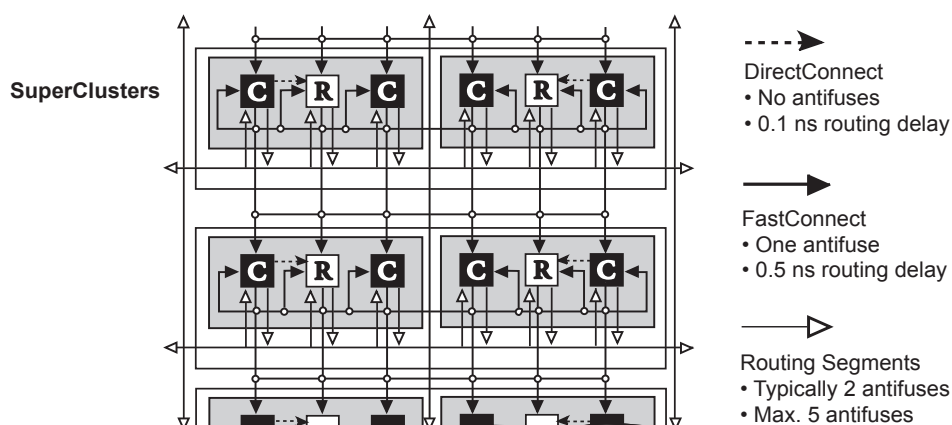
## Routing Resources

Clusters and SuperClusters can be connected through the use of two innovative local routing resources called FastConnect and DirectConnect, which enable extremely fast and predictable interconnection of modules within Clusters and SuperClusters (Figure 1-4). This routing architecture also dramatically reduces the number of antifuses required to complete a circuit, ensuring the highest possible performance.

DirectConnect is a horizontal routing resource that provides connections from a C-cell to its neighboring R-cell in a given SuperCluster. DirectConnect uses a hard-wired signal path requiring no programmable interconnection to achieve its fast signal propagation time of less than 0.1 ns (–P speed grade).

FastConnect enables horizontal routing between any two logic modules within a given SuperCluster and vertical routing with the SuperCluster immediately below it. Only one programmable connection is used in a FastConnect path, delivering maximum pin-to-pin propagation of 0.3 ns (–P speed grade).

In addition to DirectConnect and FastConnect, the architecture makes use of two globally oriented routing resources known as segmented routing and high-drive routing. The segmented routing structure of Microsemi provides a variety of track lengths for extremely fast routing between SuperClusters. The exact combination of track lengths and antifuses within each path is chosen by the fully automatic place-and-route software to minimize signal propagation delays.



**Figure 1-4 • DirectConnect and FastConnect for SuperClusters**

## Clock Resources

eX's high-drive routing structure provides three clock networks. The first clock, called HCLK, is hardwired from the HCLK buffer to the clock select MUX in each R-Cell. HCLK cannot be connected to combinational logic. This provides a fast propagation path for the clock signal, enabling the 3.9 ns clock-to-out (pad-to-pad) performance of the eX devices. The hard-wired clock is tuned to provide a clock skew of less than 0.1 ns worst case. If not used, the HCLK pin must be tied LOW or HIGH and must not be left floating. Figure 1-5 describes the clock circuit used for the constant load HCLK.

HCLK does not function until the fourth clock cycle each time the device is powered up to prevent false output levels due to any possible slow power-on-reset signal and fast start-up clock circuit. To activate HCLK from the first cycle, the TRST pin must be reserved in the Design software and the pin must be tied to GND on the board. (See the "TRST, I/O Boundary Scan Reset Pin" on page 1-32).

The remaining two clocks (CLKA, CLKB) are global routed clock networks that can be sourced from external pins or from internal logic signals (via the CLKINT routed clock buffer) within the eX device. CLKA and CLKB may be connected to sequential cells or to combinational logic. If CLKA or CLKB is sourced from internal logic signals, the external clock pin cannot be used for any other input and must be tied LOW or HIGH and must not float. Figure 1-6 describes the CLKA and CLKB circuit used in eX devices.

## Other Architectural Features

### Performance

The combination of architectural features described above enables eX devices to operate with internal clock frequencies exceeding 350 MHz for very fast execution of complex logic functions. The eX family is an optimal platform upon which the functionality previously contained in CPLDs can be integrated. eX devices meet the performance goals of gate arrays, and at the same time, present significant improvements in cost and time to market. Using timing-driven place-and-route tools, designers can achieve highly deterministic device performance.

### User Security

Microsemi FuseLock advantage provides the highest level of protection in the FPGA industry against unauthorized modifications. In addition to the inherent strengths of the architecture, special security fuses that are intended to prevent internal probing and overwriting are hidden throughout the fabric of the device. They are located such that they cannot be accessed or bypassed without destroying the rest of the device, making Microsemi antifuse FPGAs highly resistant to both invasive and more subtle noninvasive attacks.

Look for this symbol to ensure your valuable IP is secure. The FuseLock Symbol on the FPGA ensures that the device is safeguarded to cryptographic attacks.



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**Figure 1-7 • FuseLock**

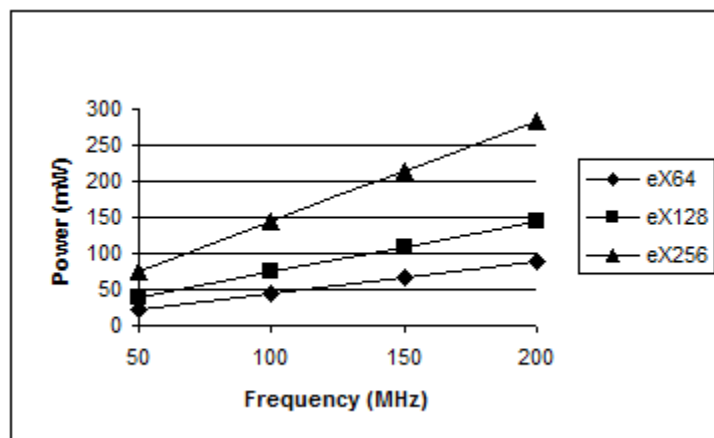
For more information, refer to [Implementation of Security in Microsemi Antifuse FPGAs](#) application note.

### I/O Modules

Each I/O on an eX device can be configured as an input, an output, a tristate output, or a bidirectional pin. Even without the inclusion of dedicated I/O registers, these I/Os, in combination with array registers, can achieve clock-to-out (pad-to-pad) timing as fast as 3.9 ns. I/O cells in eX devices do not contain embedded latches or flip-flops and can be inferred directly from HDL code. The device can easily interface with any other device in the system, which in turn enables parallel design of system components and reduces overall design time.

All unused I/Os are configured as tristate outputs by Microsemi's Designer software, for maximum flexibility when designing new boards or migrating existing designs. Each I/O module has an available pull-up or pull-down resistor of approximately 50 k $\Omega$  that can configure the I/O in a known state during power-up. Just shortly before  $V_{CCA}$  reaches 2.5 V, the resistors are disabled and the I/Os will be controlled by user logic.

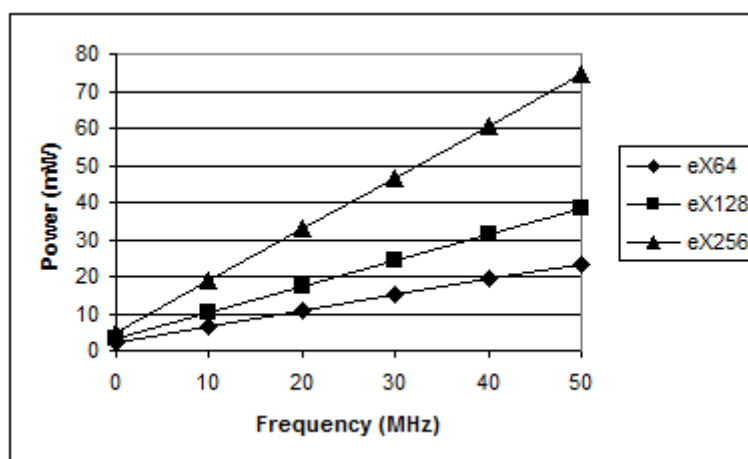
Figure 1-8 to Figure 1-11 on page 1-9 show some sample power characteristics of eX devices.



**Notes:**

1. Device filled with 16-bit counters.
2. VCCA, VCCI = 2.7 V, device tested at room temperature.

**Figure 1-8 • eX Dynamic Power Consumption – High Frequency**



**Notes:**

1. Device filled with 16-bit counters.
2. VCCA, VCCI = 2.7 V, device tested at room temperature.

**Figure 1-9 • eX Dynamic Power Consumption – Low Frequency**

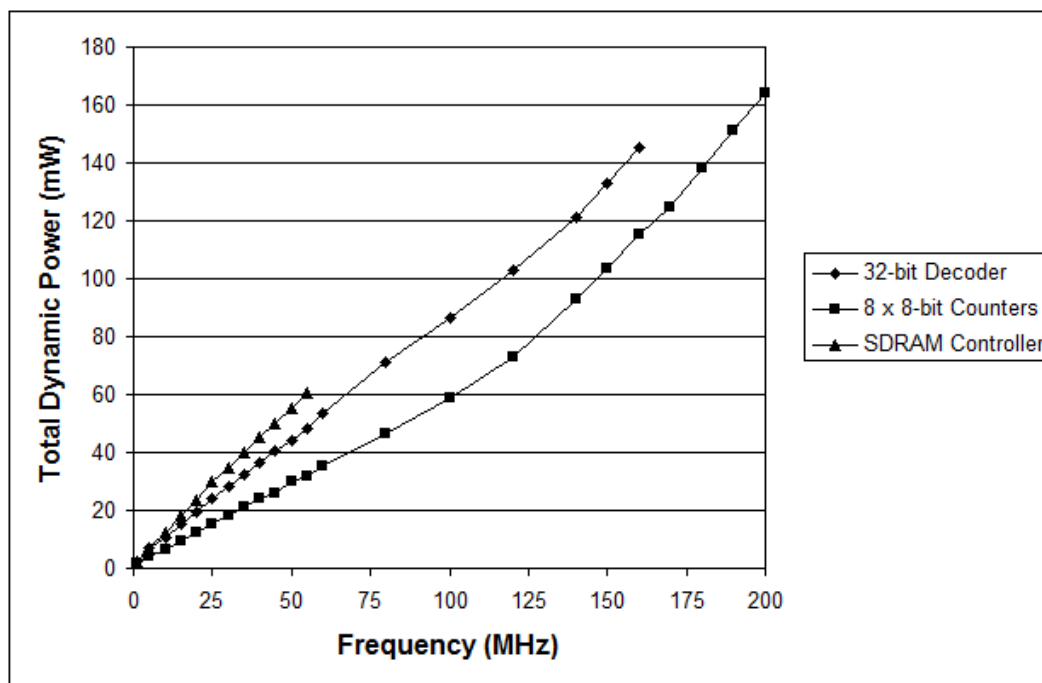


Figure 1-10 • Total Dynamic Power (mW)

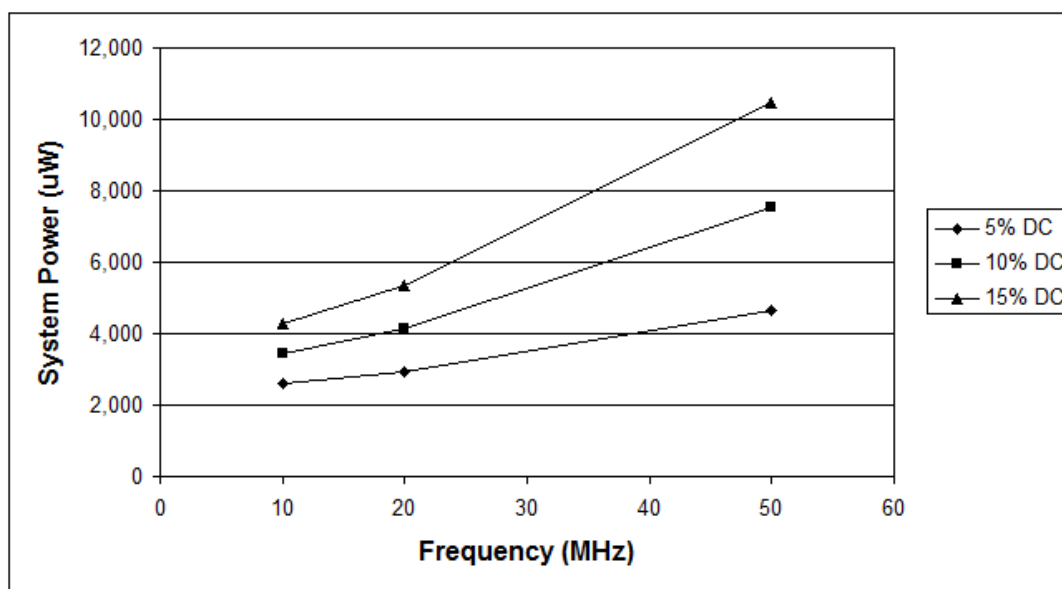


Figure 1-11 • System Power at 5%, 10%, and 15% Duty Cycle

Table 1-5 describes the different configuration requirements of BST pins and their functionality in different modes.

**Table 1-5 • Boundary-Scan Pin Configurations and Functions**

Mode	Designer "Reserve JTAG" Selection	TAP Controller State
Dedicated (JTAG)	Checked	Any
Flexible (User I/O)	Unchecked	Test-Logic-Reset
Flexible (JTAG)	Unchecked	Any EXCEPT Test-Logic-Reset

## TRST Pin

The TRST pin functions as a dedicated Boundary-Scan Reset pin when the **Reserve JTAG Test Reset** option is selected, as shown in Figure 1-12. An internal pull-up resistor is permanently enabled on the TRST pin in this mode. It is recommended to connect this pin to GND in normal operation to keep the JTAG state controller in the Test-Logic-Reset state. When JTAG is being used, it can be left floating or be driven HIGH.

When the **Reserve JTAG Test Reset** option is not selected, this pin will function as a regular I/O. If unused as an I/O in the design, it will be configured as a tristated output.

## JTAG Instructions

Table 1-6 lists the supported instructions with the corresponding IR codes for eX devices.

**Table 1-6 • JTAG Instruction Code**

Instructions (IR4: IR0)	Binary Code
EXTEST	00000
SAMPLE / PRELOAD	00001
INTTEST	00010
USERCODE	00011
IDCODE	00100
HIGHZ	01110
CLAMP	01111
Diagnostic	10000
BYPASS	11111
Reserved	All others

Table 1-7 lists the codes returned after executing the IDCODE instruction for eX devices. Note that bit 0 is always "1." Bits 11-1 are always "02F", which is Microsemi SoC Products Group's manufacturer code.

**Table 1-7 • IDCODE for eX Devices**

Device	Revision	Bits 31-28	Bits 27-12
eX64	0	8	40B2, 42B2
eX128	0	9	40B0, 42B0
eX256	0	9	40B5, 42B5
eX64	1	A	40B2, 42B2
eX128	1	B	40B0, 42B0
eX256	1	B	40B5, 42B5

## Design Considerations

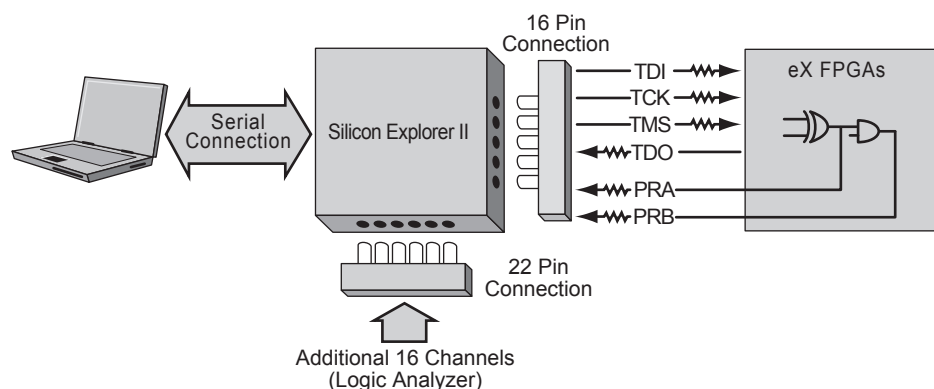
The TDI, TCK, TDO, PRA, and PRB pins should not be used as input or bidirectional ports. Since these pins are active during probing, critical signals input through these pins are not available while probing. In addition, the Security Fuse should not be programmed because doing so disables the probe circuitry. It is recommended to use a series 70Ω termination resistor on every probe connector (TDI, TCK, TMS, TDO, PRA, PRB). The 70Ω series termination is used to prevent data transmission corruption during probing and reading back the checksum.

**Table 1-8 • Device Configuration Options for Probe Capability (TRST pin reserved)**

JTAG Mode	TRST <sup>1</sup>	Security Fuse Programmed	PRA, PRB <sup>2</sup>	TDI, TCK, TDO <sup>2</sup>
Dedicated	LOW	No	User I/O <sup>3</sup>	Probing Unavailable
Flexible	LOW	No	User I/O <sup>3</sup>	User I/O <sup>3</sup>
Dedicated	HIGH	No	Probe Circuit Outputs	Probe Circuit Inputs
Flexible	HIGH	No	Probe Circuit Outputs	Probe Circuit Inputs
–	–	Yes	Probe Circuit Secured	Probe Circuit Secured

### Notes:

1. If TRST pin is not reserved, the device behaves according to TRST = HIGH in the table.
2. Avoid using the TDI, TCK, TDO, PRA, and PRB pins as input or bidirectional ports. Since these pins are active during probing, input signals will not pass through these pins and may cause contention.
3. If no user signal is assigned to these pins, they will behave as unused I/Os in this mode. Unused pins are automatically tristated by Microsemi Designer software.



**Figure 1-13 • Silicon Explorer II Probe Setup**

## Development Tool Support

The eX family of FPGAs is fully supported by both Libero® Integrated Design Environment and Designer FPGA Development software. Libero IDE is a design management environment that streamlines the design flow. Libero IDE provides an integrated design manager that seamlessly integrates design tools while guiding the user through the design flow, managing all design and log files, and passing necessary design data among tools. Additionally, Libero IDE allows users to integrate both schematic and HDL synthesis into a single flow and verify the entire design in a single environment. Libero IDE includes Synplify® for Microsemi from Synplify®, ViewDraw for Microsemi from Mentor Graphics, ModelSim® HDL Simulator from Mentor Graphics®, WaveFormer Lite™ from SynaptiCAD™, and Designer software from Microsemi. Refer to the [Libero IDE flow](#) (located on Microsemi SoC Product Group's website) diagram for more information.



## 2.5 V / 3.3 V / 5.0 V Operating Conditions

**Table 1-9 • Absolute Maximum Ratings\***

Symbol	Parameter	Limits	Units
VCCI	DC Supply Voltage for I/Os	−0.3 to +6.0	V
VCCA	DC Supply Voltage for Array	−0.3 to +3.0	V
VI	Input Voltage	−0.5 to +5.75	V
VO	Output Voltage	−0.5 to +V <sub>CCI</sub>	V
T <sub>STG</sub>	Storage Temperature	−65 to +150	°C

**Note:** \*Stresses beyond those listed under “Absolute Maximum Ratings” may cause permanent damage to the device. Exposure to absolute maximum rated conditions for extended periods may affect device reliability. Devices should not be operated outside the Recommended Operating Conditions.

**Table 1-10 • Recommended Operating Conditions**

Parameter	Commercial	Industrial	Units
Temperature Range*	0 to +70	−40 to +85	°C
2.5V Power Supply Range (VCCA, VCCI)	2.3 to 2.7	2.3 to 2.7	V
3.3V Power Supply Range (VCCI)	3.0 to 3.6	3.0 to 3.6	V
5.0V Power Supply Range (VCCI)	4.75 to 5.25	4.75 to 5.25	V

**Note:** \*Ambient temperature (T<sub>A</sub>).

**Table 1-11 • Typical eX Standby Current at 25°C**

Product	VCCA = 2.5 V VCCI = 2.5 V	VCCA = 2.5 V VCCI = 3.3 V	VCCA = 2.5 V VCCI = 5.0 V
eX64	397 μA	497 μA	700 μA
eX128	696 μA	795 μA	1,000 μA
eX256	698 μA	796 μA	2,000 μA

### 3.3 V LVTTTL Electrical Specifications

Symbol	Parameter		Commercial		Industrial		Units
			Min.	Max.	Min.	Max.	
VOH	VCCI = MIN, VI = VIH or VIL	(IOH = -8 mA)	2.4		2.4		V
VOL	VCCI = MIN, VI = VIH or VIL	(IOL = 12 mA)		0.4		0.4	V
VIL	Input Low Voltage			0.8		0.8	V
VIH	Input High Voltage		2.0	VCCI +0.5	2.0	VCCI +0.5	V
IIL/ IIH	Input Leakage Current, VIN = VCCI or GND		-10	10	-10	10	μA
IOZ	3-State Output Leakage Current, VOUT = VCCI or GND		-10	10	-10	10	μA
t <sub>R</sub> , t <sub>F1,2</sub>	Input Transition Time			10		10	ns
C <sub>IO</sub>	I/O Capacitance			10		10	pF
ICC <sup>3,4</sup>	Standby Current			1.5		10	mA
IV Curve	Can be derived from the IBIS model at <a href="http://www.microsemi.com/soc/custsup/models/ibis.html">www.microsemi.com/soc/custsup/models/ibis.html</a> .						

**Notes:**

1.  $t_R$  is the transition time from 0.8 V to 2.0 V.
2.  $t_F$  is the transition time from 2.0 V to 0.8 V.
3. ICC max Commercial -F = 5.0 mA
4. ICC = ICCI + ICCA
5. JTAG pins comply with LVTTTL/TTL I/O specification regardless of whether they are used as a user I/O or a JTAG I/O.

### 5.0 V TTL Electrical Specifications

Symbol	Parameter		Commercial		Industrial		Units
			Min.	Max.	Min.	Max.	
VOH	VCCI = MIN, VI = VIH or VIL	(IOH = -8 mA)	2.4		2.4		V
VOL	VCCI = MIN, VI = VIH or VIL	(IOL = 12 mA)		0.4		0.4	V
VIL	Input Low Voltage			0.8		0.8	V
VIH	Input High Voltage		2.0	VCCI +0.5	2.0	VCCI +0.5	V
IIL/ IIH	Input Leakage Current, VIN = VCCI or GND		-10	10	-10	10	μA
IOZ	3-State Output Leakage Current, VOUT = VCCI or GND		-10	10	-10	10	μA
t <sub>R</sub> , t <sub>F1,2</sub>	Input Transition Time			10		10	ns
C <sub>IO</sub>	I/O Capacitance			10		10	pF
ICC <sup>3,4</sup>	Standby Current			15		20	mA
IV Curve	Can be derived from the IBIS model at <a href="http://www.microsemi.com/soc/custsup/models/ibis.html">www.microsemi.com/soc/custsup/models/ibis.html</a> .						

**Note:**

1.  $t_R$  is the transition time from 0.8 V to 2.0 V.
2.  $t_F$  is the transition time from 2.0 V to 0.8 V.
3. ICC max Commercial -F=20mA
4. ICC = ICCI + ICCA
5. JTAG pins comply with LVTTTL/TTL I/O specification regardless of whether they are used as a user I/O or a JTAG I/O.

## Power Dissipation

Power consumption for eX devices can be divided into two components: static and dynamic.

### Static Power Component

The power due to standby current is typically a small component of the overall power. Typical standby current for eX devices is listed in the [Table 1-11 on page 1-16](#). For example, the typical static power for eX128 at 3.3 V  $V_{CCI}$  is:

$$I_{CC} * V_{CCA} = 795 \mu A * 2.5 V = 1.99 mW$$

### Dynamic Power Component

Power dissipation in CMOS devices is usually dominated by the dynamic power dissipation. This component is frequency-dependent and a function of the logic and the external I/O. Dynamic power dissipation results from charging internal chip capacitance due to PC board traces and load device inputs. An additional component of the dynamic power dissipation is the totem pole current in the CMOS transistor pairs. The net effect can be associated with an equivalent capacitance that can be combined with frequency and voltage to represent dynamic power dissipation.

$$\text{Dynamic power dissipation} = C_{EQ} * V_{CCA}^2 * F$$

where:

$C_{EQ}$  = Equivalent capacitance

$F$  = switching frequency

Equivalent capacitance is calculated by measuring  $I_{CCA}$  at a specified frequency and voltage for each circuit component of interest. Measurements have been made over a range of frequencies at a fixed value of VCC. Equivalent capacitance is frequency-independent, so the results can be used over a wide range of operating conditions. Equivalent capacitance values are shown below.

### CEQ Values for eX Devices

Combinatorial modules ( $C_{eqcm}$ )	1.70 pF
Sequential modules ( $C_{eqsm}$ )	1.70 pF
Input buffers ( $C_{eqi}$ )	1.30 pF
Output buffers ( $C_{eqo}$ )	7.40 pF
Routed array clocks ( $C_{eqcr}$ )	1.05 pF

The variable and fixed capacitance of other device components must also be taken into account when estimating the dynamic power dissipation.

[Table 1-12](#) shows the capacitance of the clock components of eX devices.

**Table 1-12 • Capacitance of Clock Components of eX Devices**

	eX64	eX128	eX256
Dedicated array clock – variable ( $C_{eqhv}$ )	0.85 pF	0.85 pF	0.85 pF
Dedicated array clock – fixed ( $C_{eqhf}$ )	18.00 pF	20.00 pF	25.00 pF
Routed array clock A (r1)	23.00 pF	28.00 pF	35.00 pF
Routed array clock B (r2)	23.00 pF	28.00 pF	35.00 pF

# Input Buffer Delays

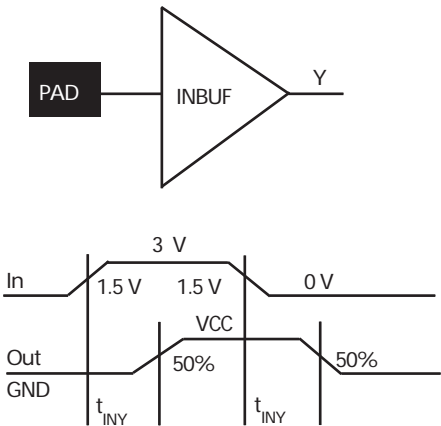


Table 1-14 • Input Buffer Delays

# C-Cell Delays

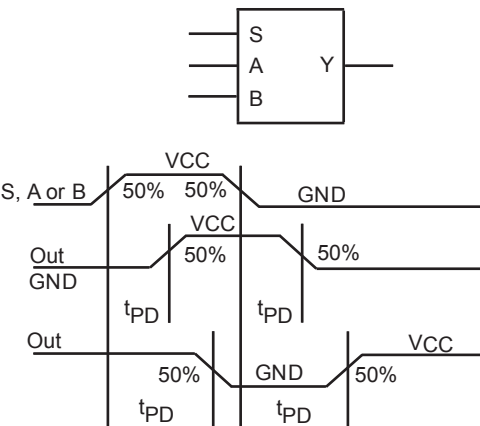
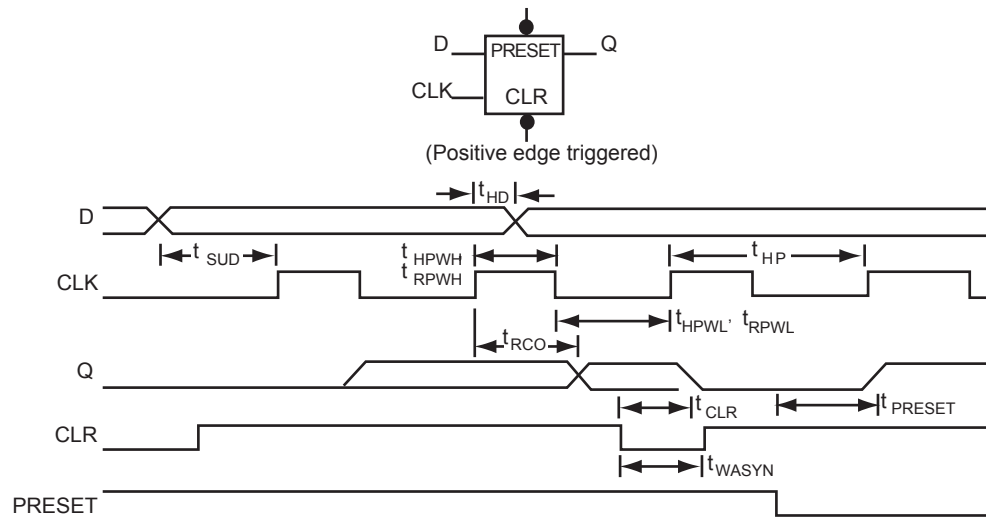


Table 1-15 • C-Cell Delays

## Cell Timing Characteristics



**Figure 1-16 • Flip-Flops**

## eX Family Timing Characteristics

**Table 1-17 • eX Family Timing Characteristics**  
(Worst-Case Commercial Conditions, VCCA = 2.3 V, T<sub>J</sub> = 70°C)

		–P Speed		Std Speed		–F Speed		Units
Parameter	Description	Min.	Max.	Min.	Max.	Min.	Max.	
C-Cell Propagation Delays <sup>1</sup>								
t <sub>PD</sub>	Internal Array Module	0.7		1.0		1.4		ns
Predicted Routing Delays <sup>2</sup>								
t <sub>DC</sub>	FO=1 Routing Delay, DirectConnect	0.1		0.1		0.2		ns
t <sub>FC</sub>	FO=1 Routing Delay, FastConnect	0.3		0.5		0.7		ns
t <sub>RD1</sub>	FO=1 Routing Delay	0.3		0.5		0.7		ns
t <sub>RD2</sub>	FO=2 Routing Delay	0.4		0.6		0.8		ns
t <sub>RD3</sub>	FO=3 Routing Delay	0.5		0.8		1.1		ns
t <sub>RD4</sub>	FO=4 Routing Delay	0.7		1.0		1.3		ns
t <sub>RD8</sub>	FO=8 Routing Delay	1.2		1.7		2.4		ns
t <sub>RD12</sub>	FO=12 Routing Delay	1.7		2.5		3.5		ns
R-Cell Timing								
t <sub>RCO</sub>	Sequential Clock-to-Q	0.6		0.9		1.3		ns
t <sub>CLR</sub>	Asynchronous Clear-to-Q	0.6		0.8		1.2		ns
t <sub>PRESET</sub>	Asynchronous Preset-to-Q	0.7		0.9		1.3		ns
t <sub>SUD</sub>	Flip-Flop Data Input Set-Up	0.5		0.7		1.0		ns
t <sub>HD</sub>	Flip-Flop Data Input Hold	0.0		0.0		0.0		ns
t <sub>WASYN</sub>	Asynchronous Pulse Width	1.3		1.9		2.6		ns
t <sub>RECA SYN</sub>	Asynchronous Recovery Time	0.3		0.5		0.7		ns
t <sub>HASYN</sub>	Asynchronous Hold Time	0.3		0.5		0.7		ns
2.5 V Input Module Propagation Delays								
t <sub>INYH</sub>	Input Data Pad-to-Y HIGH	0.6		0.9		1.3		ns
t <sub>INYL</sub>	Input Data Pad-to-Y LOW	0.8		1.1		1.5		ns
3.3 V Input Module Propagation Delays								
t <sub>INYH</sub>	Input Data Pad-to-Y HIGH	0.7		1.0		1.4		ns
t <sub>INYL</sub>	Input Data Pad-to-Y LOW	0.9		1.3		1.8		ns
5.0 V Input Module Propagation Delays								
t <sub>INYH</sub>	Input Data Pad-to-Y HIGH	0.7		1.0		1.4		ns
t <sub>INYL</sub>	Input Data Pad-to-Y LOW	0.9		1.3		1.8		ns
Input Module Predicted Routing Delays <sup>2</sup>								
t <sub>IRD1</sub>	FO=1 Routing Delay	0.3		0.4		0.5		ns
t <sub>IRD2</sub>	FO=2 Routing Delay	0.4		0.6		0.8		ns
t <sub>IRD3</sub>	FO=3 Routing Delay	0.5		0.8		1.1		ns
t <sub>IRD4</sub>	FO=4 Routing Delay	0.7		1.0		1.3		ns
t <sub>IRD8</sub>	FO=8 Routing Delay	1.2		1.7		2.4		ns
t <sub>IRD12</sub>	FO=12 Routing Delay	1.7		2.5		3.5		ns

**Notes:**

- For dual-module macros, use t<sub>PD</sub> + t<sub>RD1</sub> + t<sub>PDn</sub>, t<sub>RCO</sub> + t<sub>RD1</sub> + t<sub>PDn</sub> or t<sub>PD1</sub> + t<sub>RD1</sub> + t<sub>SUD</sub>, whichever is appropriate.
- Routing delays are for typical designs across worst-case operating conditions. These parameters should be used for estimating device performance. Post-route timing analysis or simulation is required to determine actual worst-case performance.

**Table 1-18 • eX Family Timing Characteristics**  
(Worst-Case Commercial Conditions VCCA = 2.3 V, VCCI = 4.75 V, T<sub>J</sub> = 70°C)

		–P Speed		Std Speed		–F Speed		
Parameter	Description	Min.	Max.	Min.	Max.	Min.	Max.	Units
<b>Dedicated (Hard-Wired) Array Clock Networks</b>								
t <sub>HCKH</sub>	Input LOW to HIGH (Pad to R-Cell Input)		1.1		1.6		2.3	ns
t <sub>HCKL</sub>	Input HIGH to LOW (Pad to R-Cell Input)		1.1		1.6		2.3	ns
t <sub>HPWH</sub>	Minimum Pulse Width HIGH	1.4		2.0		2.8		ns
t <sub>HPWL</sub>	Minimum Pulse Width LOW	1.4		2.0		2.8		ns
t <sub>HCKSW</sub>	Maximum Skew		<0.1		<0.1		<0.1	ns
t <sub>HP</sub>	Minimum Period	2.8		4.0		5.6		ns
f <sub>HMAX</sub>	Maximum Frequency		357		250		178	MHz
<b>Routed Array Clock Networks</b>								
t <sub>RCKH</sub>	Input LOW to HIGH (Light Load) (Pad to R-Cell Input) MAX.		1.1		1.6		2.2	ns
t <sub>RCKL</sub>	Input HIGH to LOW (Light Load) (Pad to R-Cell Input) MAX.		1.0		1.4		2.0	ns
t <sub>RCKH</sub>	Input LOW to HIGH (50% Load) (Pad to R-Cell Input) MAX.		1.2		1.7		2.4	ns
t <sub>RCKL</sub>	Input HIGH to LOW (50% Load) (Pad to R-Cell Input) MAX.		1.2		1.7		2.4	ns
t <sub>RCKH</sub>	Input LOW to HIGH (100% Load) (Pad to R-Cell Input) MAX.		1.3		1.9		2.6	ns
t <sub>RCKL</sub>	Input HIGH to LOW (100% Load) (Pad to R-Cell Input) MAX.		1.3		1.9		2.6	ns
t <sub>RPWH</sub>	Min. Pulse Width HIGH	1.5		2.1		3.0		ns
t <sub>RPWL</sub>	Min. Pulse Width LOW	1.5		2.1		3.0		ns
t <sub>RCKSW</sub> *	Maximum Skew (Light Load)		0.2		0.3		0.4	ns
t <sub>RCKSW</sub> *	Maximum Skew (50% Load)		0.1		0.2		0.3	ns
t <sub>RCKSW</sub> *	Maximum Skew (100% Load)		0.1		0.1		0.2	ns

*Note:* \*Clock skew improves as the clock network becomes more heavily loaded.

TQ64		
Pin Number	eX64 Function	eX128 Function
1	GND	GND
2	TDI, I/O	TDI, I/O
3	I/O	I/O
4	TMS	TMS
5	GND	GND
6	VCCI	VCCI
7	I/O	I/O
8	I/O	I/O
9	NC	I/O
10	NC	I/O
11	TRST, I/O	TRST, I/O
12	I/O	I/O
13	NC	I/O
14	GND	GND
15	I/O	I/O
16	I/O	I/O
17	I/O	I/O
18	I/O	I/O
19	VCCI	VCCI
20	I/O	I/O
21	PRB, I/O	PRB, I/O
22	VCCA	VCCA
23	GND	GND
24	I/O	I/O
25	HCLK	HCLK
26	I/O	I/O
27	I/O	I/O
28	I/O	I/O
29	I/O	I/O
30	I/O	I/O
31	I/O	I/O
32	TDO, I/O	TDO, I/O

TQ64		
Pin Number	eX64 Function	eX128 Function
33	GND	GND
34	I/O	I/O
35	I/O	I/O
36	VCCA	VCCA
37	VCCI	VCCI
38	I/O	I/O
39	I/O	I/O
40	NC	I/O
41	NC	I/O
42	I/O	I/O
43	I/O	I/O
44	VCCA	VCCA
45*	GND/LP	GND/ LP
46	GND	GND
47	I/O	I/O
48	I/O	I/O
49	I/O	I/O
50	I/O	I/O
51	I/O	I/O
52	VCCI	VCCI
53	I/O	I/O
54	I/O	I/O
55	CLKA	CLKA
56	CLKB	CLKB
57	VCCA	VCCA
58	GND	GND
59	PRA, I/O	PRA, I/O
60	I/O	I/O
61	VCCI	VCCI
62	I/O	I/O
63	I/O	I/O
64	TCK, I/O	TCK, I/O

*Note: \*Please read the LP pin descriptions for restrictions on their use.*



TQ100			
Pin Number	eX64 Function	eX128 Function	eX256 Function
1	GND	GND	GND
2	TDI, I/O	TDI, I/O	TDI, I/O
3	NC	NC	I/O
4	NC	NC	I/O
5	NC	NC	I/O
6	I/O	I/O	I/O
7	TMS	TMS	TMS
8	VCCI	VCCI	VCCI
9	GND	GND	GND
10	NC	I/O	I/O
11	NC	I/O	I/O
12	I/O	I/O	I/O
13	NC	I/O	I/O
14	I/O	I/O	I/O
15	NC	I/O	I/O
16	TRST, I/O	TRST, I/O	TRST, I/O
17	NC	I/O	I/O
18	I/O	I/O	I/O
19	NC	I/O	I/O
20	VCCI	VCCI	VCCI
21	I/O	I/O	I/O
22	NC	I/O	I/O
23	NC	NC	I/O
24	NC	NC	I/O
25	I/O	I/O	I/O
26	I/O	I/O	I/O
27	I/O	I/O	I/O
28	I/O	I/O	I/O
29	I/O	I/O	I/O
30	I/O	I/O	I/O
31	I/O	I/O	I/O
32	I/O	I/O	I/O
33	I/O	I/O	I/O
34	PRB, I/O	PRB, I/O	PRB, I/O
35	VCCA	VCCA	VCCA

TQ100			
Pin Number	eX64 Function	eX128 Function	eX256 Function
36	GND	GND	GND
37	NC	NC	NC
38	I/O	I/O	I/O
39	HCLK	HCLK	HCLK
40	I/O	I/O	I/O
41	I/O	I/O	I/O
42	I/O	I/O	I/O
43	I/O	I/O	I/O
44	VCCI	VCCI	VCCI
45	I/O	I/O	I/O
46	I/O	I/O	I/O
47	I/O	I/O	I/O
48	I/O	I/O	I/O
49	TDO, I/O	TDO, I/O	TDO, I/O
50	NC	I/O	I/O
51	GND	GND	GND
52	NC	NC	I/O
53	NC	NC	I/O
54	NC	NC	I/O
55	I/O	I/O	I/O
56	I/O	I/O	I/O
57	VCCA	VCCA	VCCA
58	VCCI	VCCI	VCCI
59	NC	I/O	I/O
60	I/O	I/O	I/O
61	NC	I/O	I/O
62	I/O	I/O	I/O
63	NC	I/O	I/O
64	I/O	I/O	I/O
65	NC	I/O	I/O
66	I/O	I/O	I/O
67	VCCA	VCCA	VCCA
68	GND/LP	GND/LP	GND/LP
69	GND	GND	GND
70	I/O	I/O	I/O

**Note:** \*Please read the LP pin descriptions for restrictions on their use.

TQ100			
Pin Number	eX64 Function	eX128 Function	eX256 Function
71	I/O	I/O	I/O
72	NC	I/O	I/O
73	NC	NC	I/O
74	NC	NC	I/O
75	NC	NC	I/O
76	NC	I/O	I/O
77	I/O	I/O	I/O
78	I/O	I/O	I/O
79	I/O	I/O	I/O
80	I/O	I/O	I/O
81	I/O	I/O	I/O
82	VCCI	VCCI	VCCI
83	I/O	I/O	I/O
84	I/O	I/O	I/O
85	I/O	I/O	I/O
86	I/O	I/O	I/O
87	CLKA	CLKA	CLKA
88	CLKB	CLKB	CLKB
89	NC	NC	NC
90	VCCA	VCCA	VCCA
91	GND	GND	GND
92	PRA, I/O	PRA, I/O	PRA, I/O
93	I/O	I/O	I/O
94	I/O	I/O	I/O
95	I/O	I/O	I/O
96	I/O	I/O	I/O
97	I/O	I/O	I/O
98	I/O	I/O	I/O
99	I/O	I/O	I/O
100	TCK, I/O	TCK, I/O	TCK, I/O

**Note:** \*Please read the LP pin descriptions for restrictions on their use.

Revision	Changes	Page
v4.0 (continued)	The "Flexible Mode" section was updated.	1-10
	Table 1-5 •Boundary-Scan Pin Configurations and Functions is new.	1-11
	The "TRST Pin" section was updated.	1-11
	The "Probing Capabilities" section is new.	1-12
	The "Programming" section was updated.	1-12
	The "Probing Capabilities" section was updated.	1-12
	The "Silicon Explorer II Probe" section was updated.	1-12
	The "Design Considerations" section was updated.	1-13
	The "Development Tool Support" section was updated.	1-13
	The "Absolute Maximum Ratings*" section was updated.	1-16
	The "Temperature and Voltage Derating Factors" section was updated.	1-26
	The "TDI, I/O Test Data Input" section was updated.	1-31
	The "TDO, I/O Test Data Output" section was updated.	1-31
	The "TMS Test Mode Select" section was updated.	1-32
	The "TRST, I/O Boundary Scan Reset Pin" section was updated.	1-32
	All VSV pins were changed to VCCA. The change affected the following pins: 64-Pin TQFP – Pin 36 100-Pin TQFP – Pin 57 49-Pin CSP – Pin D5 128-Pin CSP – Pin H11 and Pin J1 for eX256 180-Pin CSP – Pins J12 and K2	
v3.0	The "Recommended Operating Conditions" section has been changed.	1-16
	The "3.3 V LVTTTL Electrical Specifications" section has been updated.	1-18
	The "5.0 V TTL Electrical Specifications" section has been updated.	1-18
	The "Total Dynamic Power (mW)" section is new.	1-9
	The "System Power at 5%, 10%, and 15% Duty Cycle" section is new.	1-9
	The "eX Timing Model" section has been updated.	1-22
v2.0.1	The I/O Features table, Table 1-2 on page 1-6, was updated.	1-6
	The table, "Standby Power of eX Devices in LP Mode Typical Conditions, VCCA, VCCI = 2.5 V, T <sub>J</sub> = 25° C" section, was updated.	1-7
	"Typical eX Standby Current at 25°C" section is a new table.	1-16
	The table in the section, "Package Thermal Characteristics" section has been updated for the 49-Pin CSP.	1-21
	The "eX Timing Model" section has been updated.	1-22
	The timing numbers found in, "eX Family Timing Characteristics" section have been updated.	1-27
	The V <sub>SV</sub> pin has been added to the "Pin Description" section.	1-31
	Please see the following pin tables for the V <sub>SV</sub> pin and an important footnote including the pin: "TQ64", "TQ100", "128-Pin CSP", and "180-Pin CSP".	2-1, 2-3, 2-6, 2-11
	The figure, "TQ64" section has been updated.	2-1

## Datasheet Categories

### **Categories**

In order to provide the latest information to designers, some datasheet parameters are published before data has been fully characterized from silicon devices. The data provided for a given device, as highlighted in the ["eX Device Status" table on page II](#), is designated as either "Product Brief," "Advance," "Preliminary," or "Production." The definitions of these categories are as follows:

#### **Product Brief**

The product brief is a summarized version of a datasheet (advance or production) and contains general product information. This document gives an overview of specific device and family information.

#### **Advance**

This version contains initial estimated information based on simulation, other products, devices, or speed grades. This information can be used as estimates, but not for production. This label only applies to the DC and Switching Characteristics chapter of the datasheet and will only be used when the data has not been fully characterized.

#### **Preliminary**

The datasheet contains information based on simulation and/or initial characterization. The information is believed to be correct, but changes are possible.

#### **Production**

This version contains information that is considered to be final.

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